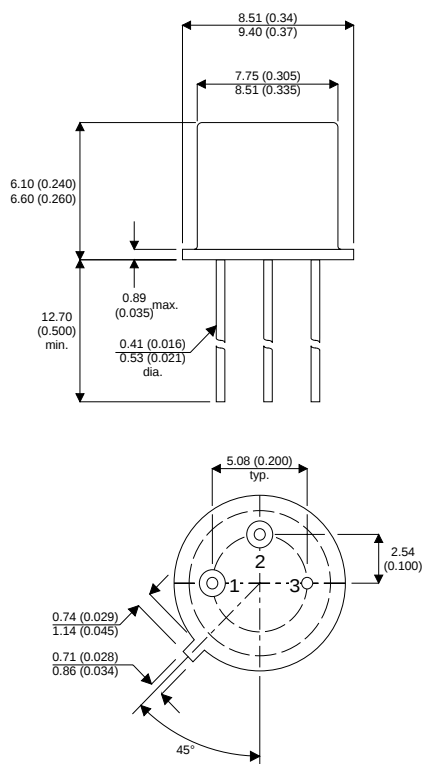


MECHANICAL DATA

Dimensions in mm (inches)



TO-39 (TO-205AD)

Pin 1 – Emitter

Pin 2 – Base

Pin 3 – Collector

PNP SILICON TRANSISTORS

DESCRIPTION

The 2N5679 and 2N5680 are silicon epitaxial planar PNP transistors in jedec TO-39 metal case intended for use as drivers for high power transistors in general purpose, amplifier and switching circuit

The complementary NPN types are the 2N5681 and 2N5682 respectively

ABSOLUTE MAXIMUM RATINGS

$T_{CASE} = 25^{\circ}C$ unless otherwise stated

T _{CASE} = 25°C unless otherwise stated		2N5679	2N5680
V _{CBO}	Collector – Base Voltage	-100V	-120V
V _{CEO}	Collector – Emitter Voltage (I _B = 0)	-100V	-120V
V _{EBO}	Emitter – Base Voltage (I _C = 0)		-4V
I _C	Continuous Collector Current		-1A
I _B	Base Current		-0.5A
P _{tot}	Total Dissipation at T _{case} ≤ 25°C		10W
	T _{amb} ≤ 25°C		1W
T _{stg}	Operating and Storage Temperature Range		-65 to +200°C
T _j	Junction temperature		200°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	17.5	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO} Collector Cut Off Current	$I_E = 0$ for 2N5679 $V_{CB} = -100V$ for 2N5680 $V_{CB} = -120V$			-1 -1	μA
I_{CEV} Collector Cut Off Current	$V_{BE} = 1.5$ for 2N5679 $V_{CE} = -100V$ for 2N5680 $V_{CE} = -120V$			-1 -1	μA
	$T_{case} = 150^{\circ}C$ for 2N5679 $V_{CE} = -100V$ for 2N5680 $V_{CE} = -120V$			-1 -1	mA
I_{CEO} Collector Cut Off Current	$I_B = 0$ for 2N5679 $V_{CE} = -70V$ for 2N5680 $V_{CE} = -80V$			-10 -10	μA
I_{EBO} Emitter Cut Off Current	$I_C = 0$ $V_{EB} = -4V$			-1	
$V_{CEO(sus)*}$ Collector Emitter Sustaining Voltage	$I_B = 0$ $I_C = -10mA$ for 2N5679 for 2N5680	-100 -120			V
$V_{CE(sat)*}$ Collector Emitter Saturation Voltage	$I_C = -250mA$ $I_B = -25mA$ $I_C = -500mA$ $I_B = -50mA$ $I_C = -1A$ $I_B = -200mA$			-0.6 -1 -2	
V_{BE*} Base Emitter Voltage	$I_C = -250mA$ $V_{CE} = -2V$			-1	
h_{FE*} DC Current Gain	$I_C = -250mA$ $V_{CE} = -2V$ $I_C = -1A$ $V_{CE} = -2V$	40 5		150	
f_T Transistion Frequency	$I_C = -100mA$ $V_{CE} = -10V$ $f = 10MHz$	30			MHz
C_{CBO} Collector Base Capacitance	$I_E = 0$ $V_{CB} = -20V$ $f = 1MHz$			50	pF
h_{fe} Small Signal Current Gain	$I_C = -0.2A$ $V_{CE} = -1.5V$ $f = 1KHz$	40			

* Pulse test $t_p = 300\mu s$, $\delta < 2\%$

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